

Product data sheet

Product profile

1.1 General description

The BFT25A is a silicon NPN transistor, primarily intended for use in RF low power amplifiers, such as pocket telephones and paging systems with signal frequencies up to 2 GHz.

The transistor is encapsulated in a 3-pin plastic SOT23 envelope.

1.2 Features and benefits

- Low current consumption (100 μA to 1 mA)
- Low noise figure
- Gold metallization ensures excellent reliability.

1.3 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-	8	V
V _{CEO}	collector-emitter voltage	open base	-	-	5	V
I _C	DC collector current		-	-	6.5	mA
P _{tot}	total power dissipation	up to $T_s = 165 ^{\circ}\text{C}$	[1] -	-	32	mW
h _{FE}	DC current gain	$I_C = 0.5 \text{ mA}; V_{CE} = 1 \text{ V}$	50	80	200	
f _T	transition frequency	$I_{C} = 1 \text{ mA}; V_{CE} = 1 \text{ V};$ $T_{amb} = 25 \text{ °C};$ f = 500 MHz	3.5	5	-	GHz
G _{UM}	maximum unilateral power gain	$I_{C} = 0.5 \text{ mA}; V_{CE} = 1 \text{ V};$ $T_{amb} = 25 ^{\circ}\text{C};$ f = 1 GHz	-	15	-	dB
F	noise figure	$\Gamma = \Gamma_{opt}$; I _C = 0.5 mA; V _{CE} = 1 V; T _{amb} = 25 °C; f = 1 GHz	-	1.8	-	dB
		$\begin{split} &\Gamma = \Gamma_{opt}; \ I_C = 1 \ mA; \\ &V_{CE} = 1 \ V; \\ &T_{amb} = 25 \ ^{\circ}C; \ f = 1 \ GHz \end{split}$	-	2	-	dB

^[1] T_s is the temperature at the soldering point of the collector tab.



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2. Pinning information

Table 2. Discrete pinning

	p		
Pin	Description	Simplified outline	Symbol
Code: V10			
1	base	3	3
2	emitter		1—
3	collector	1 2	']
			2
			svm021

3. Ordering information

Table 3. Ordering information

Type number	r Package		
	Name	Description	Version
BFT25A	-	plastic surface mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking

Type number	Marking code ^[1]
BFT25A	34*

[1] * = p: Made in Hong Kong.

* = t : Made in Malaysia.

* = W : Made in China.

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	8	V
V_{CEO}	collector-emitter voltage	open base	-	5	V
V_{EBO}	emitter-base voltage	open collector	-	2	V
I _C	DC collector current		-	6.5	mA
P _{tot}	total power dissipation	up to $T_s = 165 ^{\circ}C$	[1] -	32	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	175	°C

^[1] T_s is the temperature at the soldering point of the collector tab.

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6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-s)}$	from junction to soldering point		<u>[1]</u> 260	K/W

^[1] T_s is the temperature at the soldering point of the collector tab.

7. Characteristics

Table 7. Characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector cut-off current	$I_E = 0 A; V_{CB} = 5 V$	-	-	50	nA
h _{FE}	DC current gain	$I_C = 0.5 \text{ mA}; V_{CE} = 1 \text{ V}$	50	80	200	
f _T	transition frequency	$I_{C} = 1 \text{ mA}; V_{CE} = 1 \text{ V};$ $T_{amb} = 25 \text{ °C};$ f = 500 MHz	3.5	5	-	GHz
C _{re}	feedback capacitance	$I_C = I_c = 0 A; V_{CB} = 1 V;$ f = 1 MHz	-	0.3	0.45	pF
G _{UM}	maximum unilateral power gain	$I_{C} = 0.5 \text{ mA}; V_{CE} = 1 \text{ V};$ $T_{amb} = 25 ^{\circ}\text{C}; f = 1 \text{ GHz}$	[1] -	15	-	dB
F	noise figure	$\begin{split} \Gamma &= \Gamma_{opt}; \ I_C = 0.5 \ mA; \\ V_{CE} &= 1 \ V; \\ T_{amb} &= 25 \ ^{\circ}C; \ f = 1 \ GHz \end{split}$	-	1.8	-	dB
		$\begin{split} &\Gamma = \Gamma_{opt}; \ I_C = 1 \ mA; \\ &V_{CE} = 1 \ V; \\ &T_{amb} = 25 \ ^{\circ}C; \ f = 1 \ GHz \end{split}$	-	2	-	dB

^[1] $\;\;G_{UM}$ is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{\text{UM}} = 10 \log \frac{\left|S_{21}\right|^2}{(I - \left|S_{11}\right|^2)(I - \left|S_{22}\right|^2)} dB$$

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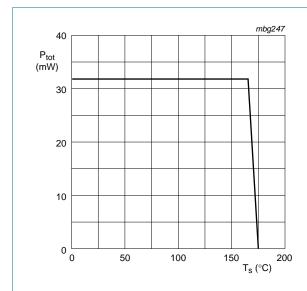
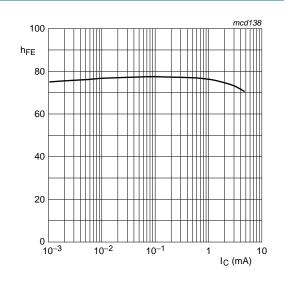


Fig 1. Power derating curve.



 $V_{CE} = 1 V.$

Fig 2. DC current gain as a function of collector current.

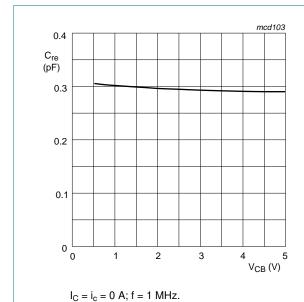
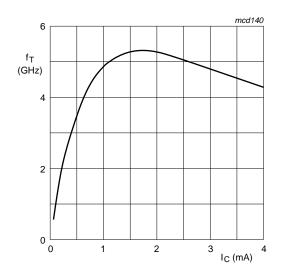


Fig 3. Feedback capacitance as a function of collector-base voltage.

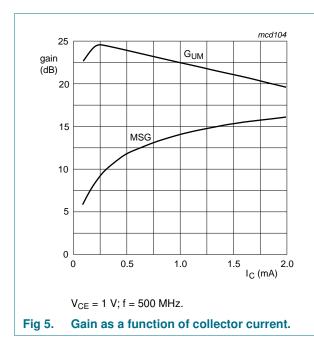


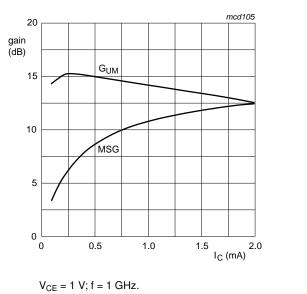
 V_{CE} = 1 V; T_{amb} = 25 °C; f = 500 MHz.

Fig 4. Transition frequency as a function of collector current.

<u>Figure 5, 6, 7</u> and 8, G_{UM} = maximum unilateral power gain; MSG = maximum stable gain.

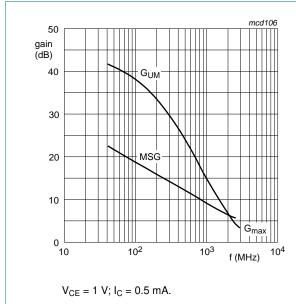
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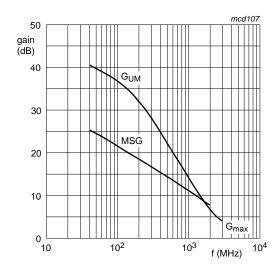




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Fig 6. Gain as a function of collector current.





 $V_{CE} = 1 \text{ V}; I_{C} = 1 \text{ mA}.$

Fig 7. Gain as a function of frequency.

Fig 8. Gain as a function of frequency.

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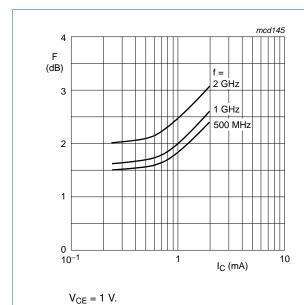


Fig 9. Minimum noise figure as a function of collector current.

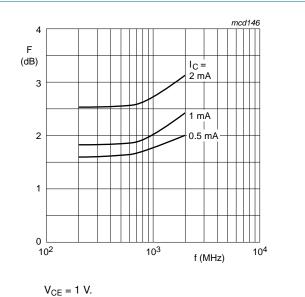


Fig 10. Minimum noise figure as a function of frequency.

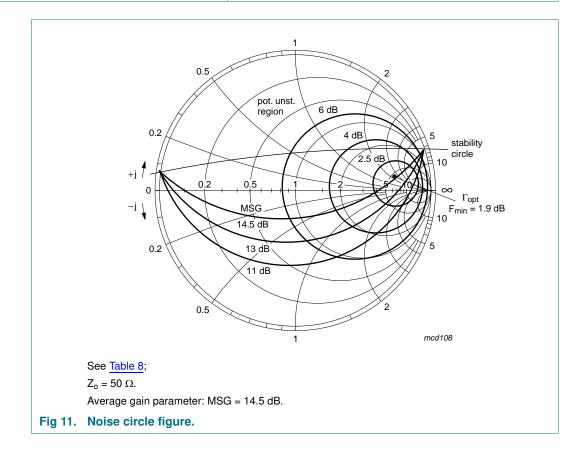


Table 8. Noise parameters

f (MHz)	V _{CE} (V)	I _C (mA)	F _{min} (dB)	Γ_{opt}		R _n /50
				(mag)	(ang)	
500	1	1	1.9	0.79	4	2.5

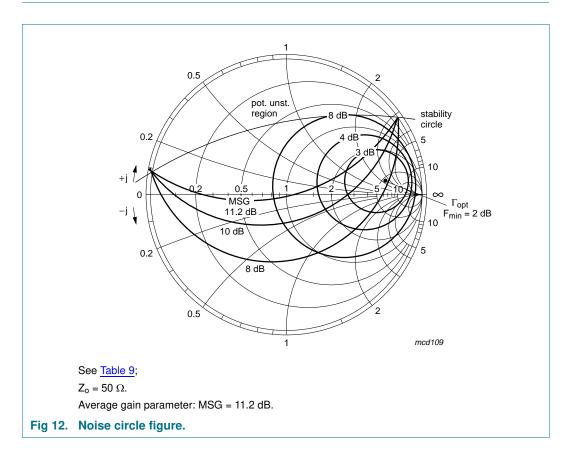


Table 9. Noise parameters

f (MHz)	V _{CE} (V)	I _C (mA)	F _{min} (dB)	Γ_{opt}		R _n /50
				(mag)	(ang)	
1000	1	1	2	0.74	8	2.6

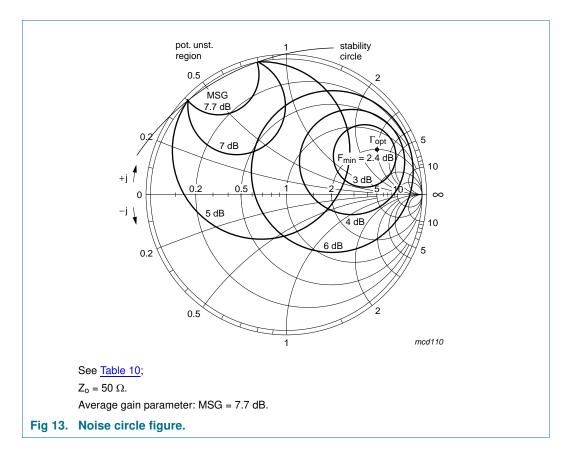
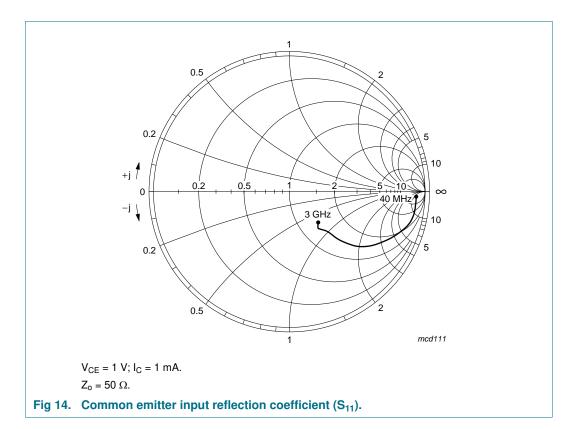
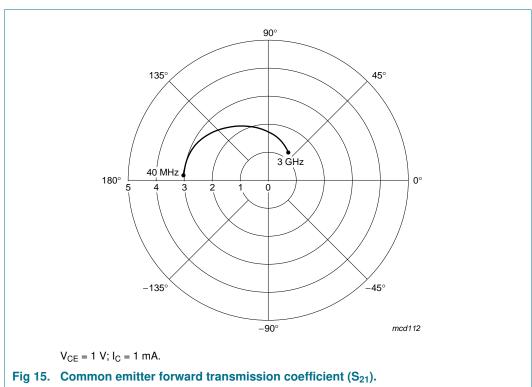
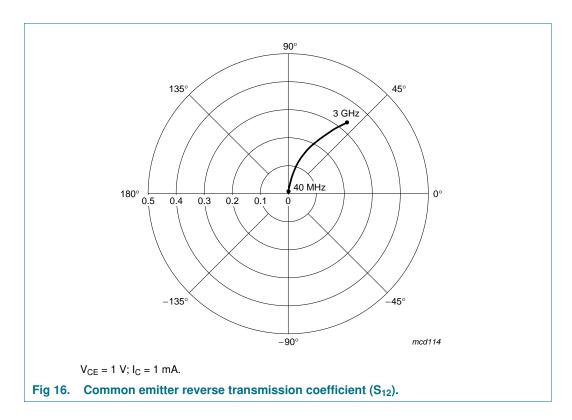


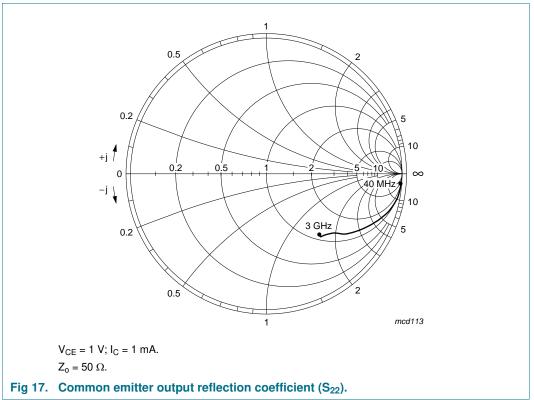
Table 10. Noise parameters

f (MHz)	V _{CE} (V)	I _C (mA)	F _{min} (dB)	Γ_{opt}		R _n /50
				(mag)	(ang)	
2000	1	1	2.4	0.72	26	1.7









8. Package outline

Plastic surface-mounted package; 3 leads SOT23 В Α Χ = v M A 3 **→** | w (M) B е detail X 0 1 2 **DIMENSIONS (mm are the original dimensions)** UNIT D Ε Q e₁ H_{E} L_p w max. 0.48 0.45 1.1 1.4 1.2 0.15 3.0 0.55 0.1 0.9 0.38 0.09 2.8 0.15 REFERENCES **EUROPEAN** OUTLINE ISSUE DATE VERSION JEDEC **PROJECTION** IEC **JEITA**

Fig 18. Package outline.

SOT23

TO-236AB

-04-11-04

06-03-16

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9. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BFT25A v.5	20110912	Product data sheet	-	BFT25A v.4		
Modifications:	guidelines o	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 				
	· ·	 Legal texts have been adapted to the new company name where appropriate. 				
	 Package ou 	utline drawings have been u	pdated to the latest vers	sion.		
BFT25A v.4 (9397 750 13399)	20040706	Product data sheet	-	BFT25A_CNV v.3		
BFT25A_CNV v.3	19971205	Product specification	-	-		

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10. Legal information

10.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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